

2SJ351, 2SJ352

Silicon P-Channel MOS FET

Application

Low frequency power amplifier
Complementary pair with 2SK2220
2SK2221

Features

- High power gain
- Excellent frequency response
- High speed switching
- Wide area of safe operation
- Enhancement-mode
- Good complementary characteristics
- Equipped with gate protection diodes

Table 1 Ordering Information

Type No.	V _{DSS}
2SJ351	-180 V
2SJ352	-200 V

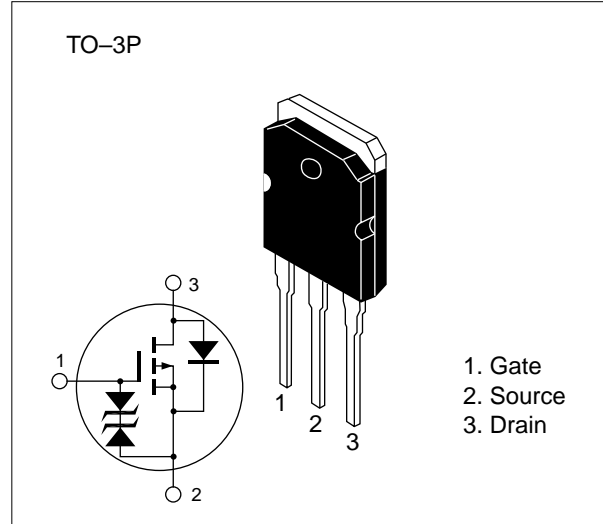


Table 2 Absolute Maximum Ratings (T_a = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SJ351	V _{DSX}	-180	V
	2SJ352		-200	
Gate to source voltage		V _{GSS}	±20	V
Drain current		I _D	-8	A
Body-drain diode reverse drain current		I _{DR}	-8	A
Channel dissipation		P _{ch} *	100	W
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to +150	°C

* Value at T_c = 25 °C

Table 3 Electrical Characteristics (Ta = 25°C)

Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SJ351	$V_{(BR)DSX}$	-180	—	—	V	$I_D = -10 \text{ mA}, V_{GS} = 10 \text{ V}$
	2SJ352		-200	—	—		
Gate to source breakdown voltage		$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100 \mu\text{A}, V_{DS} = 0$
Gate to source cutoff voltage		$V_{GS(off)}$	-0.15	—	-1.45	V	$I_D = -100 \text{ mA}$ $V_{DS} = -10 \text{ V}$
Drain to source saturation voltage		$V_{DS(sat)}$	—	—	-12	V	$I_D = -8 \text{ A}, V_{GD} = 0 \text{ V}^*$
Forward transfer admittance		$ y_{fs} $	0.7	1.0	1.4	S	$I_D = -3 \text{ A}$ $V_{DS} = -10 \text{ V}^*$
Input capacitance		C_{iss}	—	800	—	pF	$V_{GS} = 5 \text{ V}$
Output capacitance		C_{oss}	—	1000	—	pF	$V_{DS} = -10 \text{ V}$
Reverse transfer capacitance		C_{rss}	—	18	—	pF	$f = 1 \text{ MHz}$
Turn-on time		t_{on}	—	320	—	ns	$V_{DD} = -30 \text{ V}$
Turn-off time		t_{off}	—	120	—	ns	$I_D = -4 \text{ A}$

* Pulse Test

